

# **Report on GEM Standalone Simulation Studies**

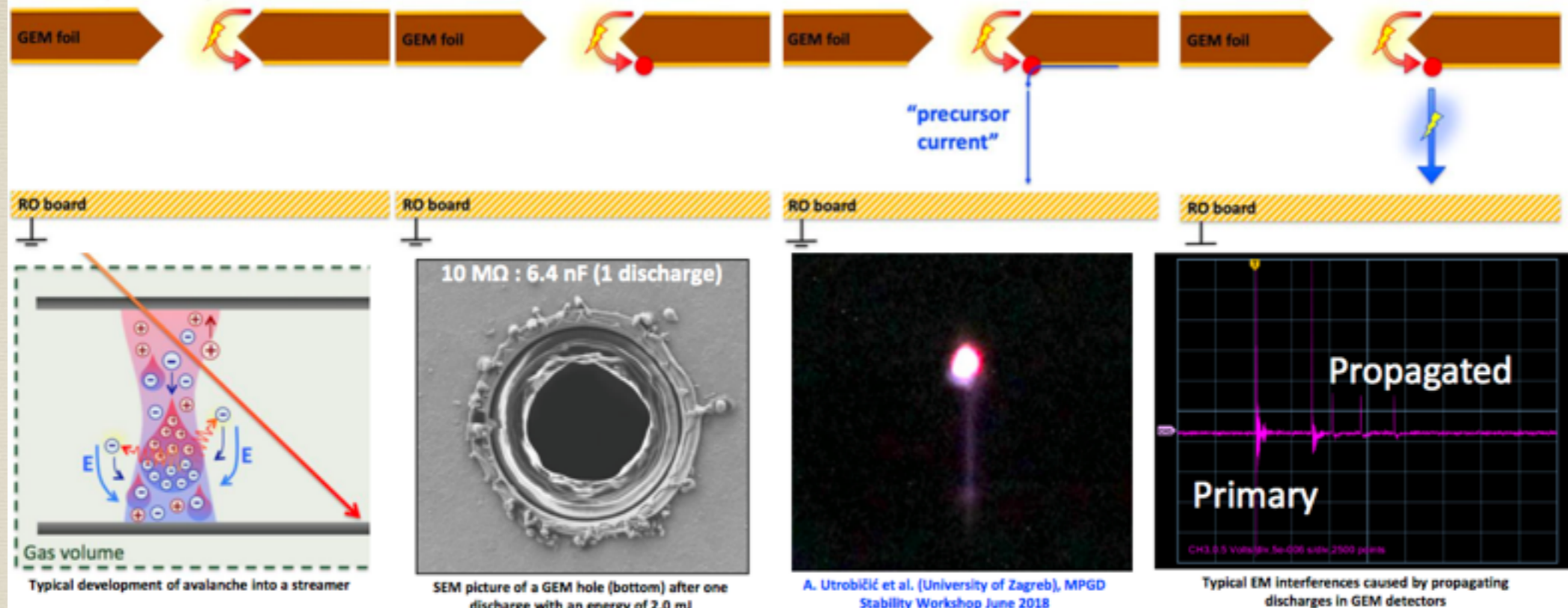
Shivali Malhotra on behalf of  
**GEM Detector Simulation  
group**

**GEM Workshop, Sep 30 - Oct 4, 2019**

# GE1/1 Operation



## Discharge Propagation Principle



- **Step 1:** Primary discharged caused by the increase of the space charge density in the avalanche

- **Step 2:** Creation of a hot spot on the copper near the hole rim  $>2500\text{ }^{\circ}\text{C}$

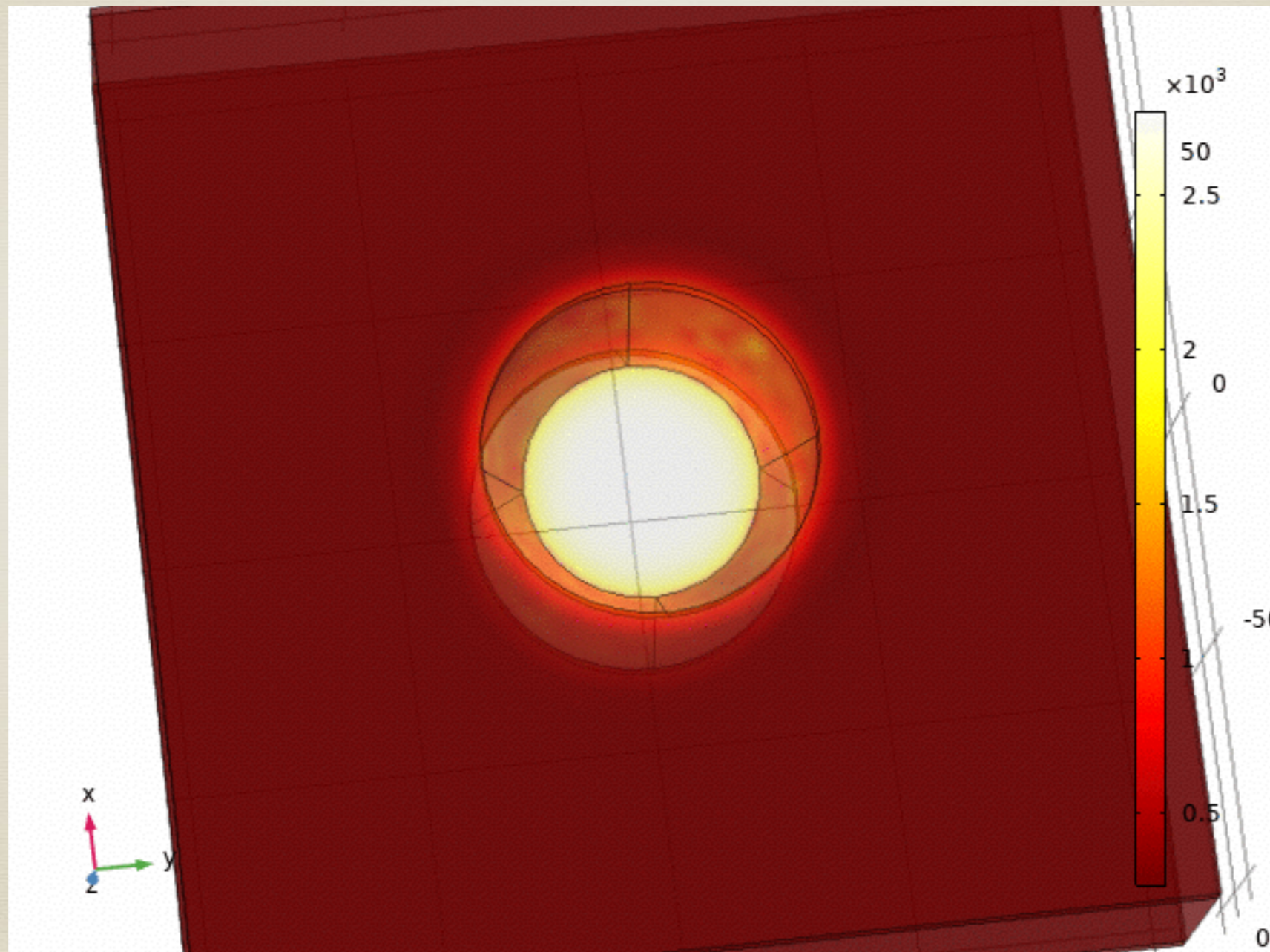
- **Step 3:** Thermionic emission of electrons in the gas, enhanced by local electric field (Schottky effect)

- **Step 4:** Development of the precursor current into a streamer causing a second discharge

Extensive study initiated by Alice and RD51 communities (Technical University of Munich, University of Zagreb et al.)

# Heat Transfer Study

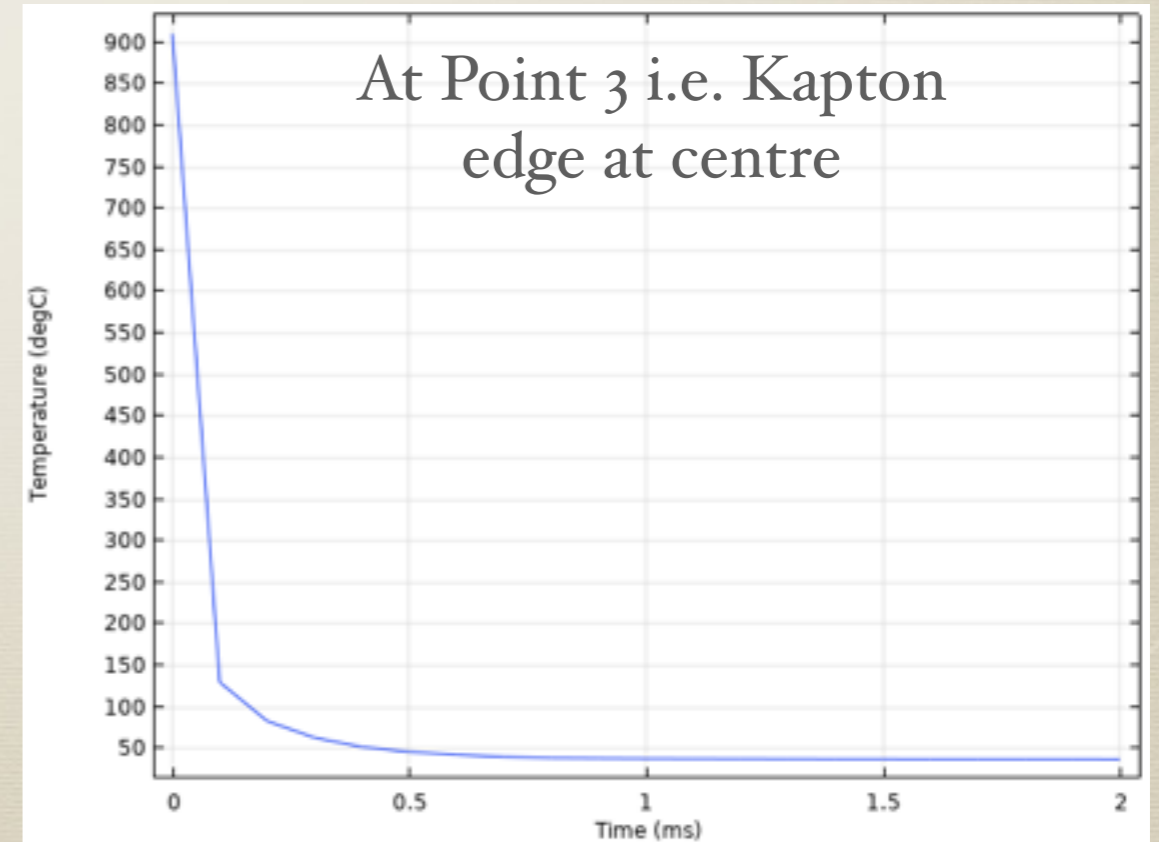
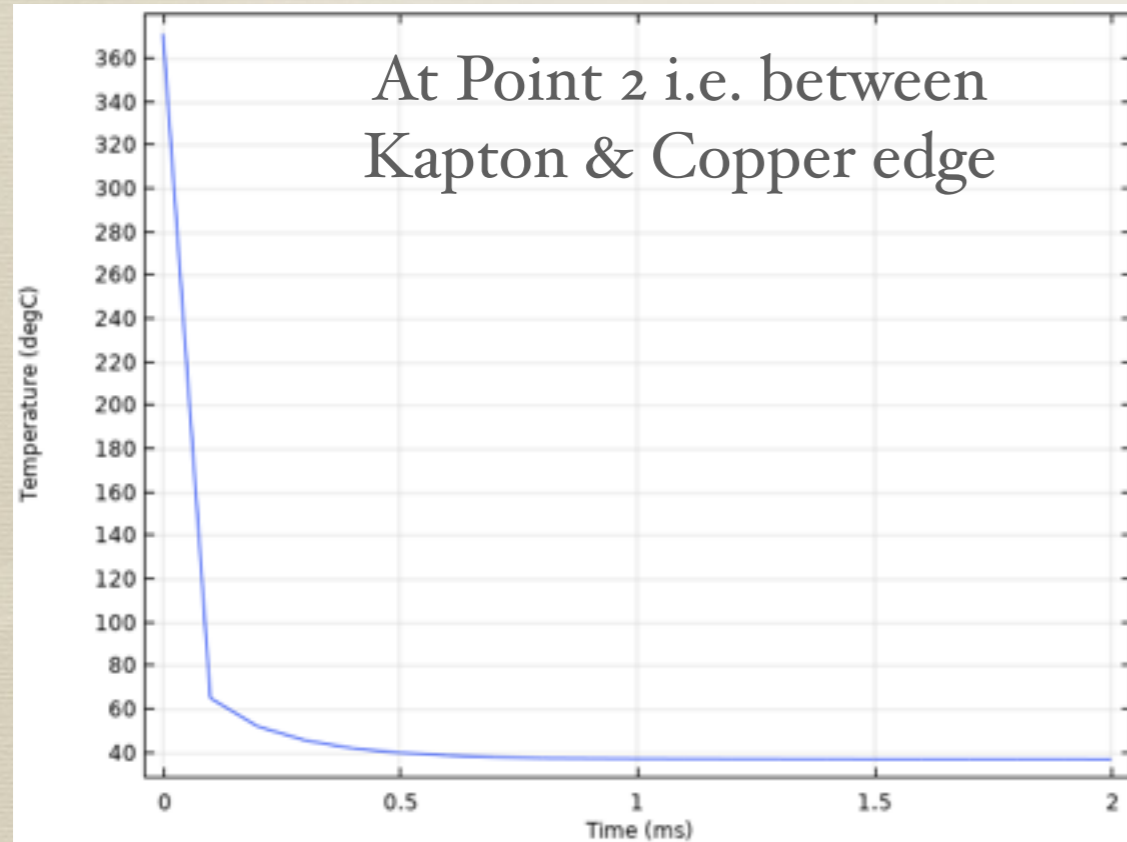
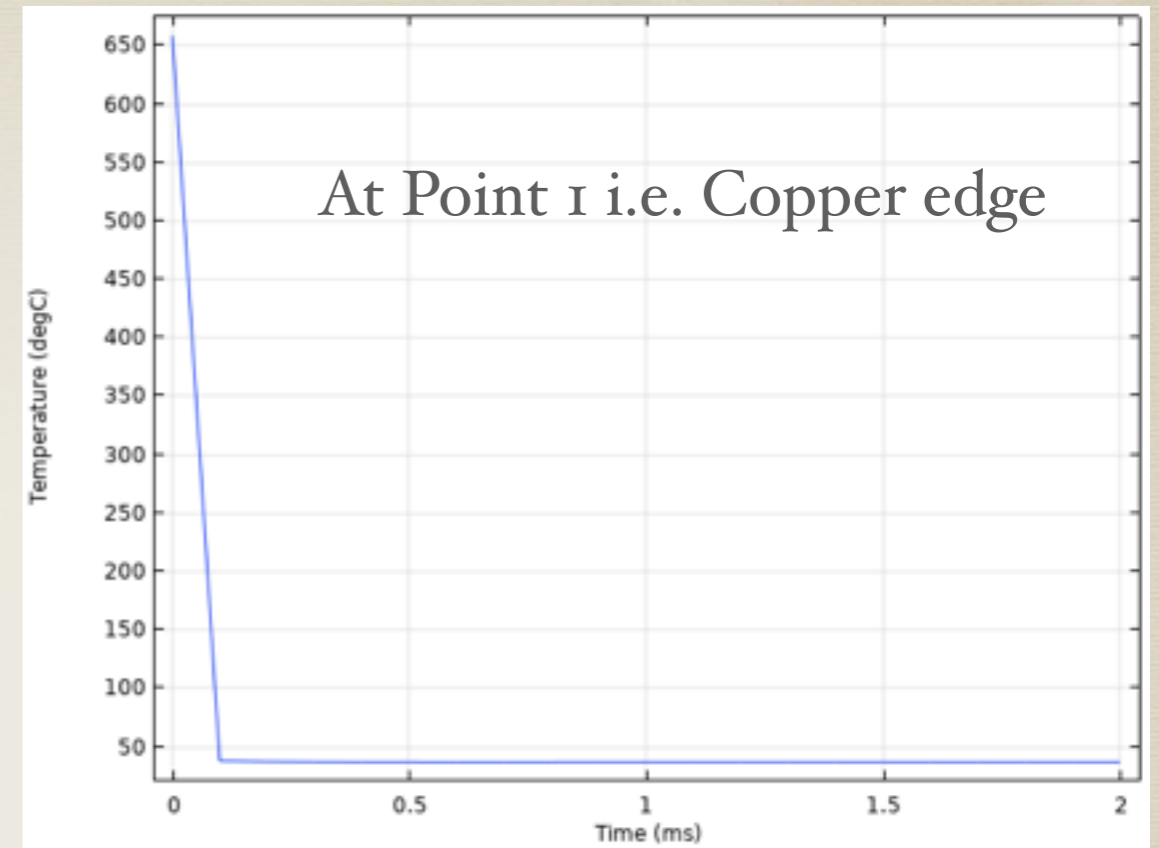
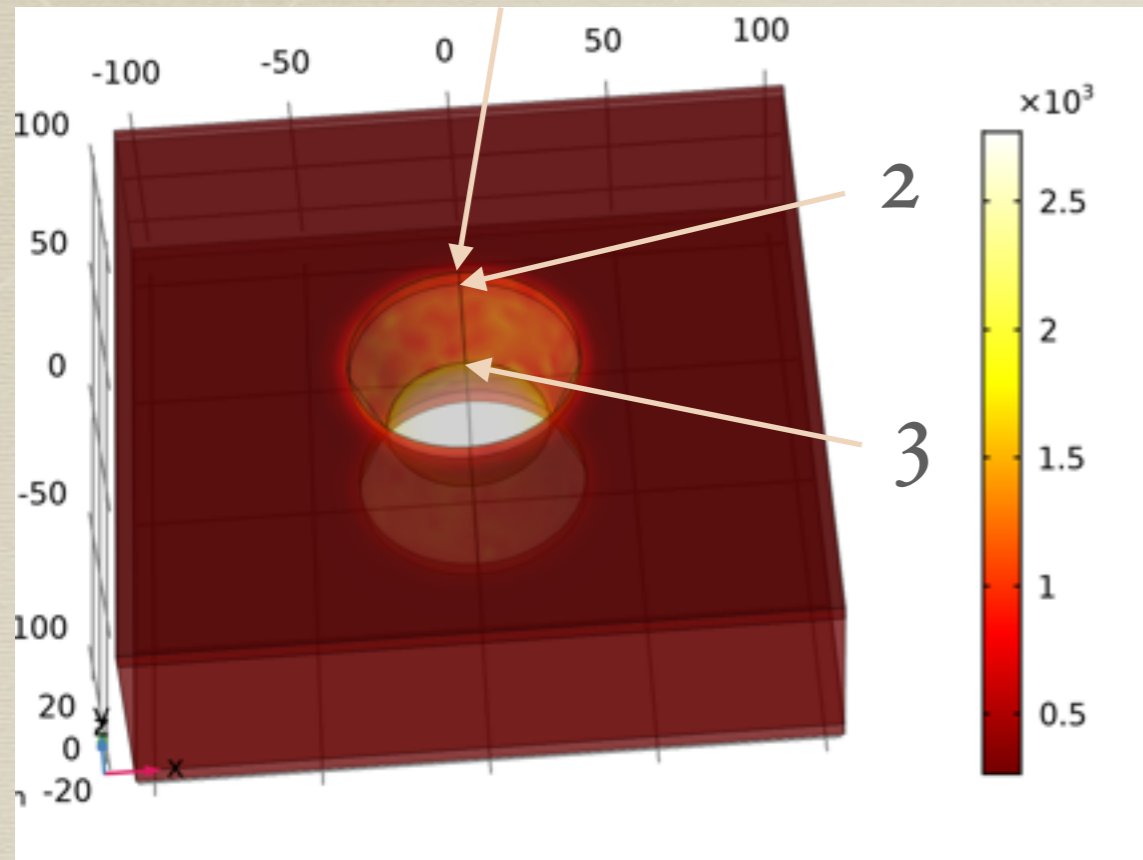
3-D Model of a single hole GEM foil with 2500 °C inside hole



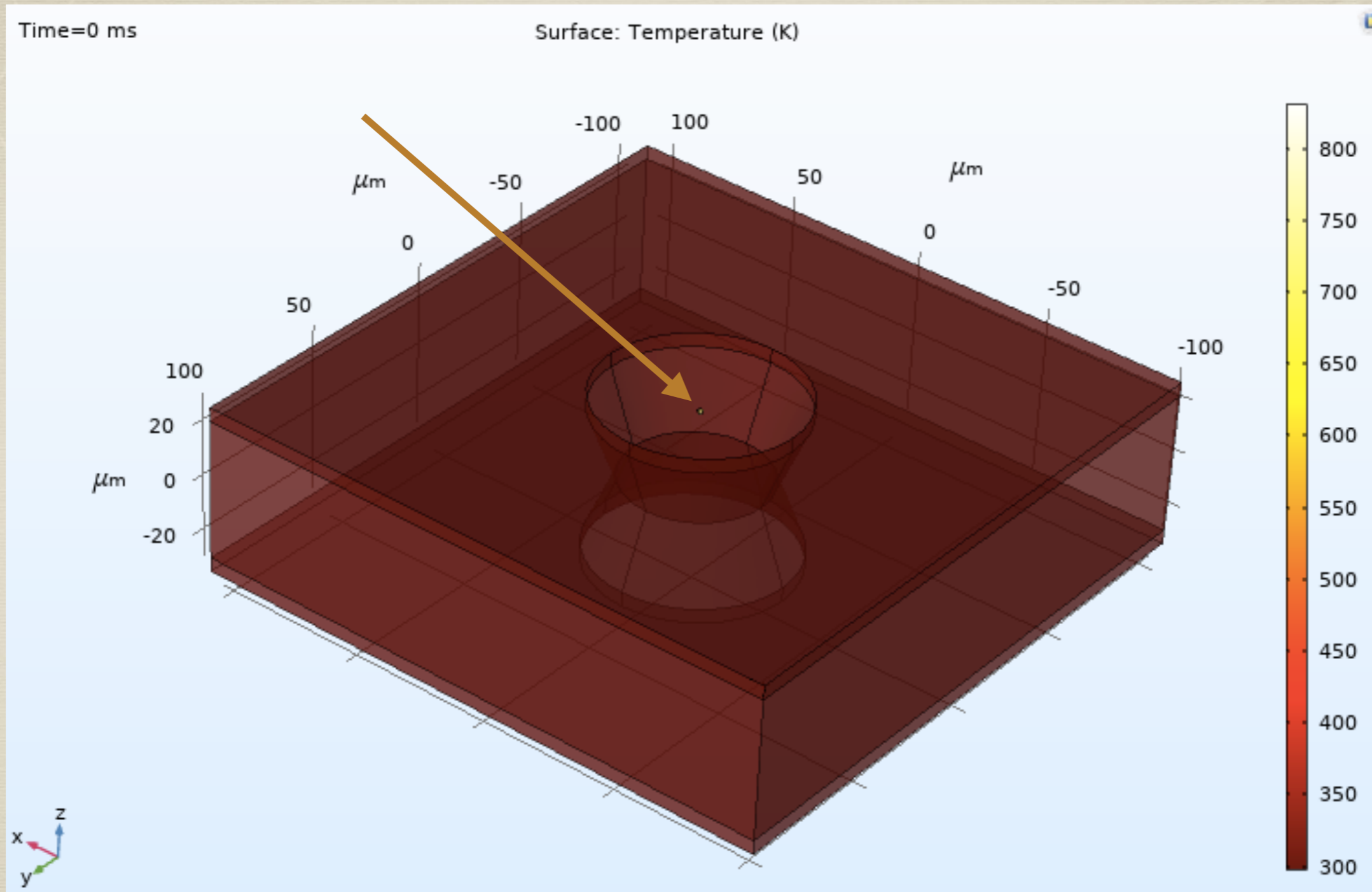
Time dependent solution using COMSOL Multi physics

# Variation of Temperature with Time

I



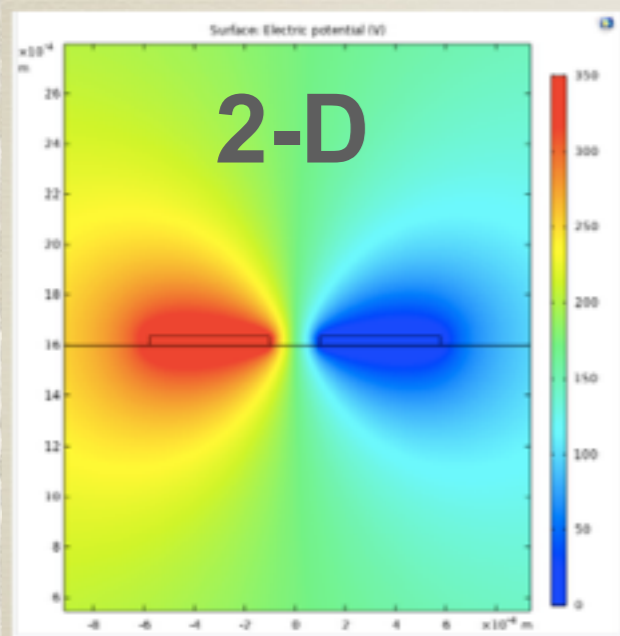
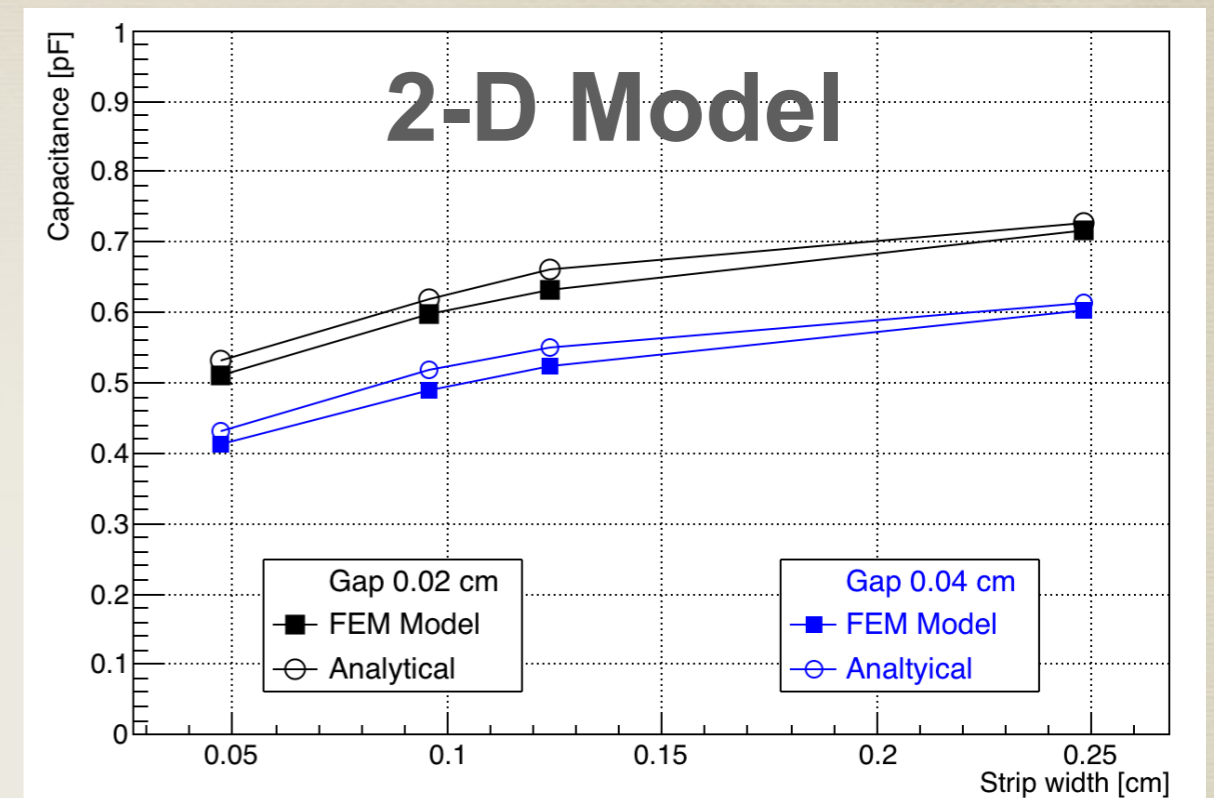
# Temperature with Point Source



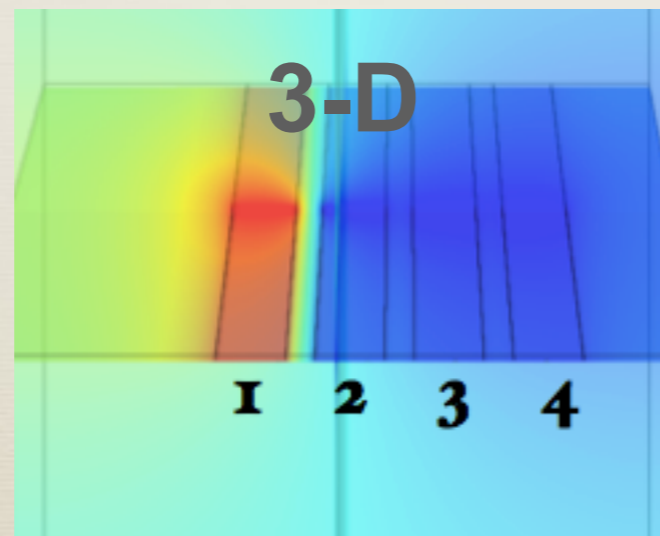
Made an initial condition of heat coming from a point source at 2500 °C but acc. to the simulation it shows only 550 °C.

# Interstrip Capacitance (GE2/1)

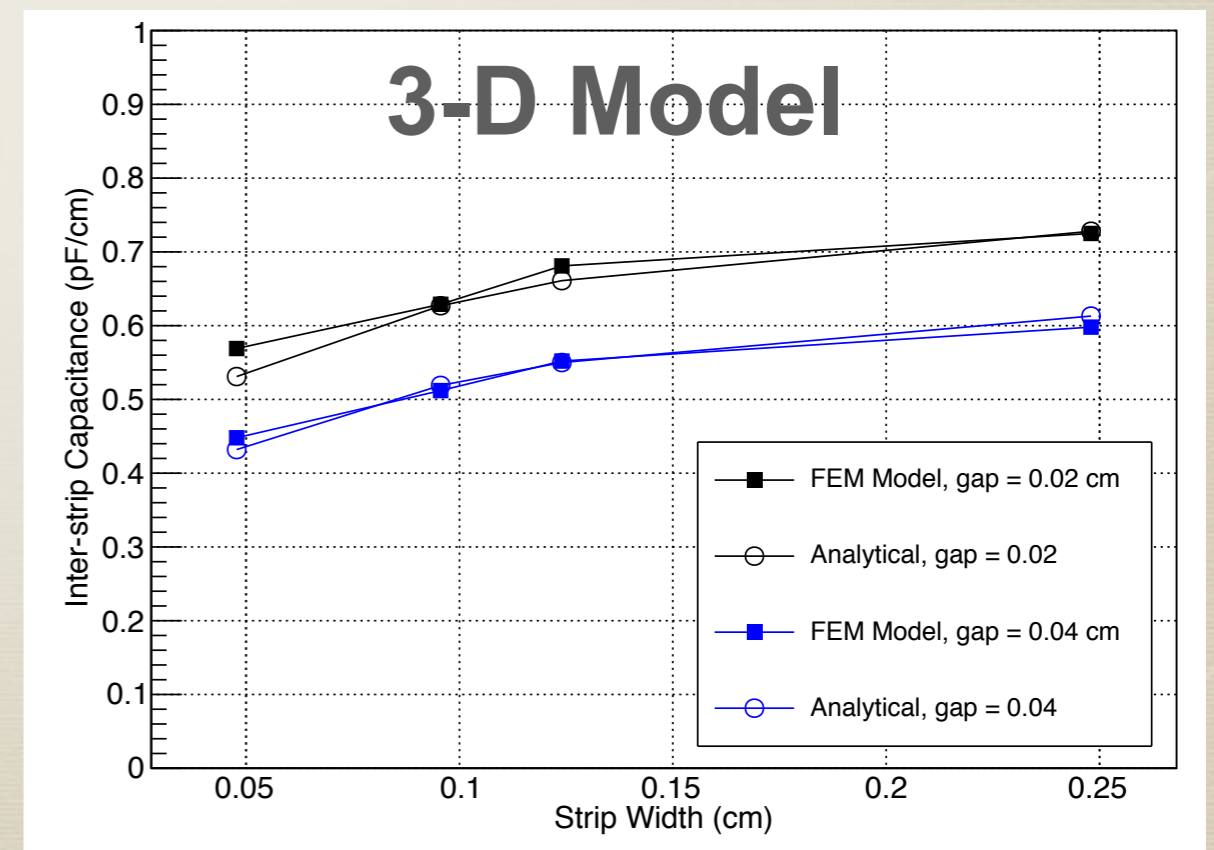
- Build a FEM for two strips
- First using MATLAB and now COMSOL for multi-strips
- Compared results for  $M_1$  &  $M_4$  size strips with analytical calculations (CMS IN-2018/006)
- Extended 2-D model to 3-D with 2, 3 and 4 strips using COMSOL



$C_{21} = 0.5108 \text{ pF}$   
 Strip width = 0.0478 cm  
 Gap width = 0.02 cm



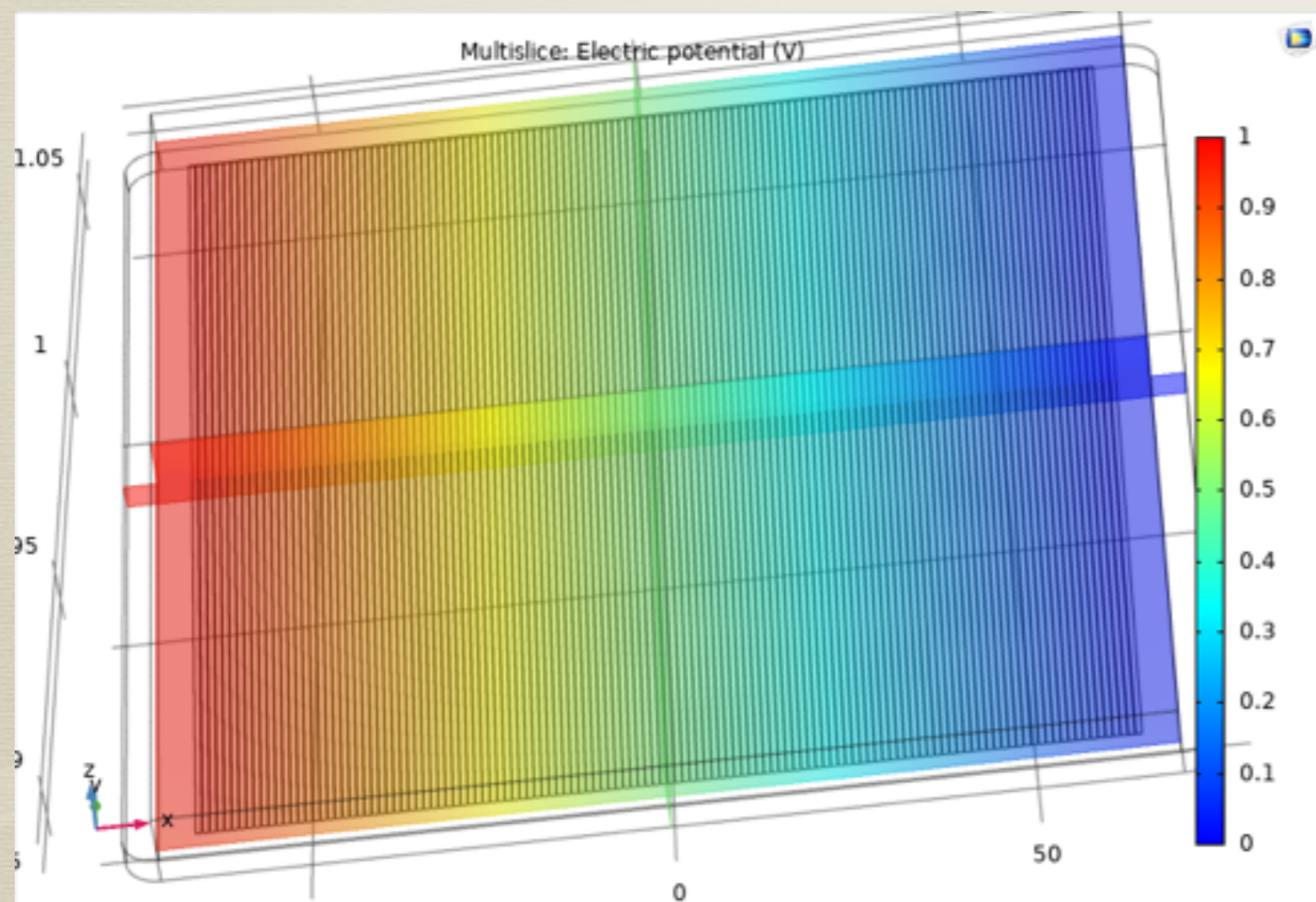
$C_{21} = 0.401 \text{ pF/cm}$   
 $C_{31} = 0.093 \text{ pF/cm}$   
 $C_{41} = 0.085 \text{ pF/cm}$



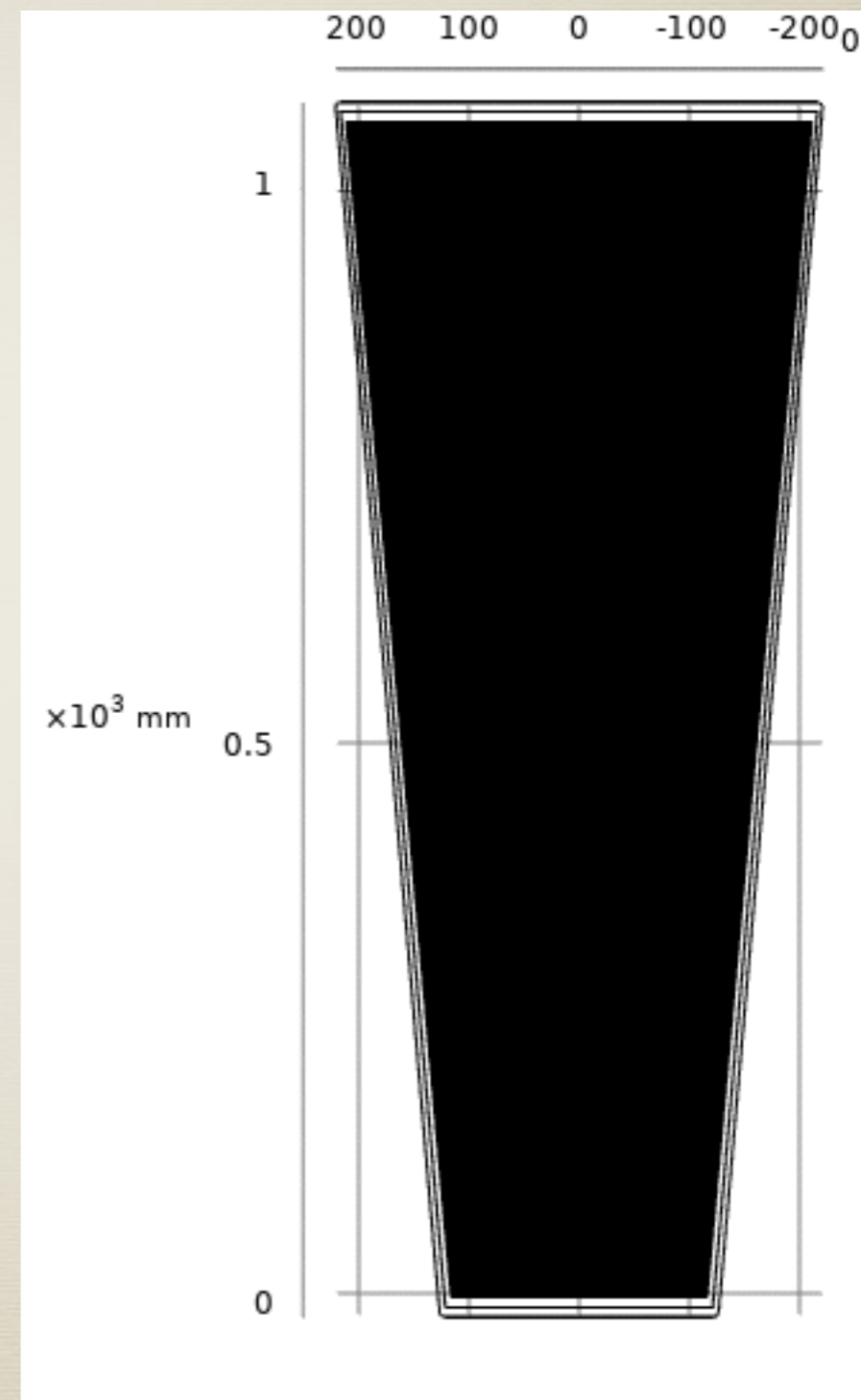
# Interstrip Capacitance

- Impossible to do meshing of whole GE1/1 readout board
- Tried to do scan for each eta sector but still required more computing power
- Decided to use only 128 strips model

## GE1/1 RO Board



Sector I with 128 strips



# Interstrip Capacitance (GE1/1)

Calculated and experimentally measured values of Interstrip capacitance of GE1/I-X-S RO Board (from CMS IN-2018/006)

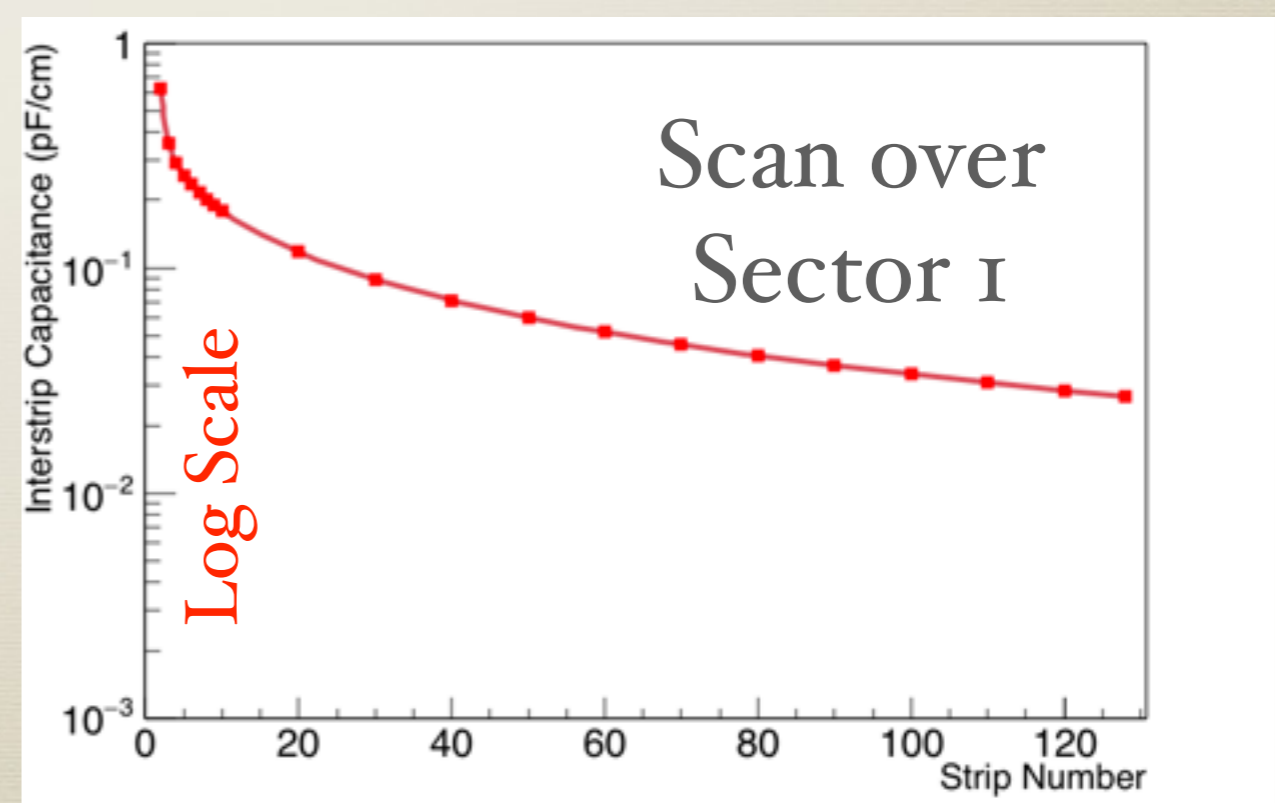
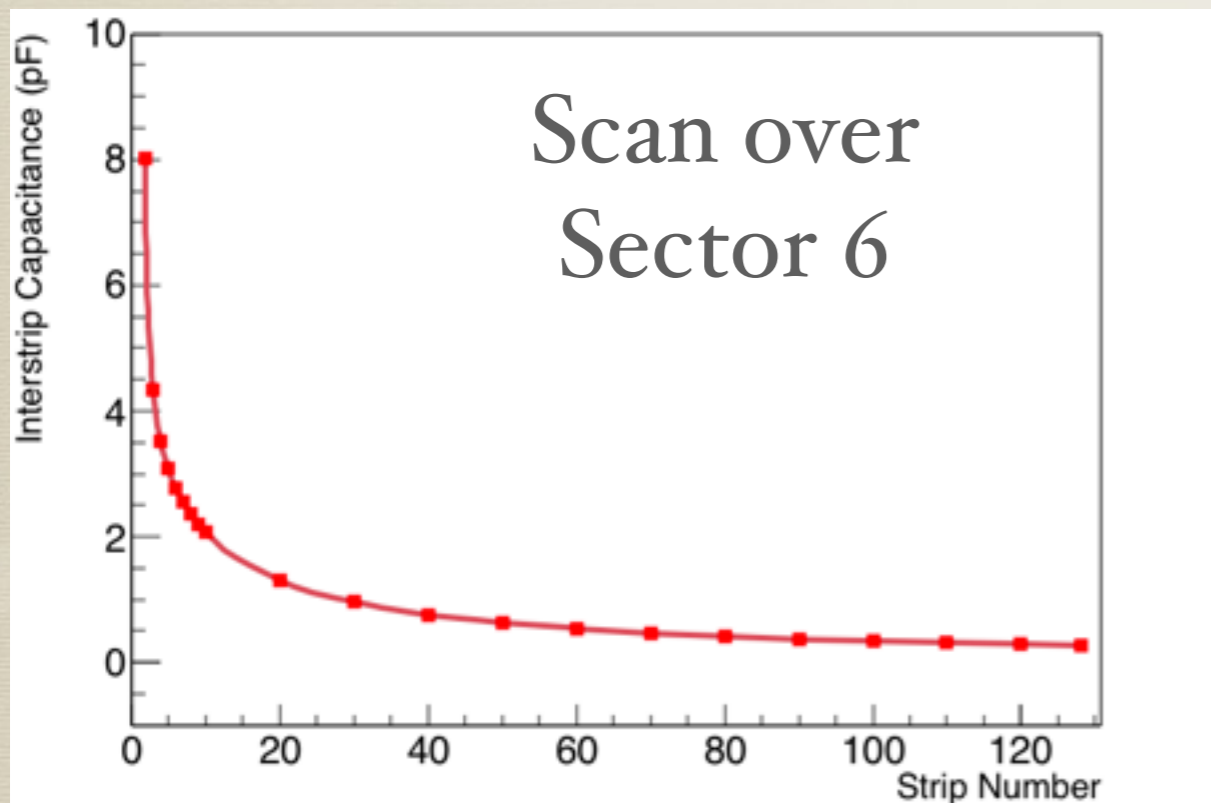
| Eta Sector               | 1          | 2           | 3           | 4          | 5          | 6          | 7           | 8           |
|--------------------------|------------|-------------|-------------|------------|------------|------------|-------------|-------------|
| Calc. Cap./cm (pF/cm)    | 0.624      | 0.598       | 0.585       | 0.571      | 0.555      | 0.545      | 0.529       | 0.515       |
| Avg. Meas. (pF/cm)       | 1.02       | 0.946       | 0.942       | 1.01       | 1.04       | 1.00       | 0.909       | 0.952       |
| Meas. Error (pF/cm)      | $\pm 0.08$ | $\pm 0.084$ | $\pm 0.086$ | $\pm 0.10$ | $\pm 0.16$ | $\pm 0.11$ | $\pm 0.128$ | $\pm 0.187$ |
| Ratio (Calc./Avg. Meas.) | 0.61       | 0.63        | 0.62        | 0.57       | 0.54       | 0.54       | 0.58        | 0.54        |

Using COMSOL (pF/cm) 0.769

0.710

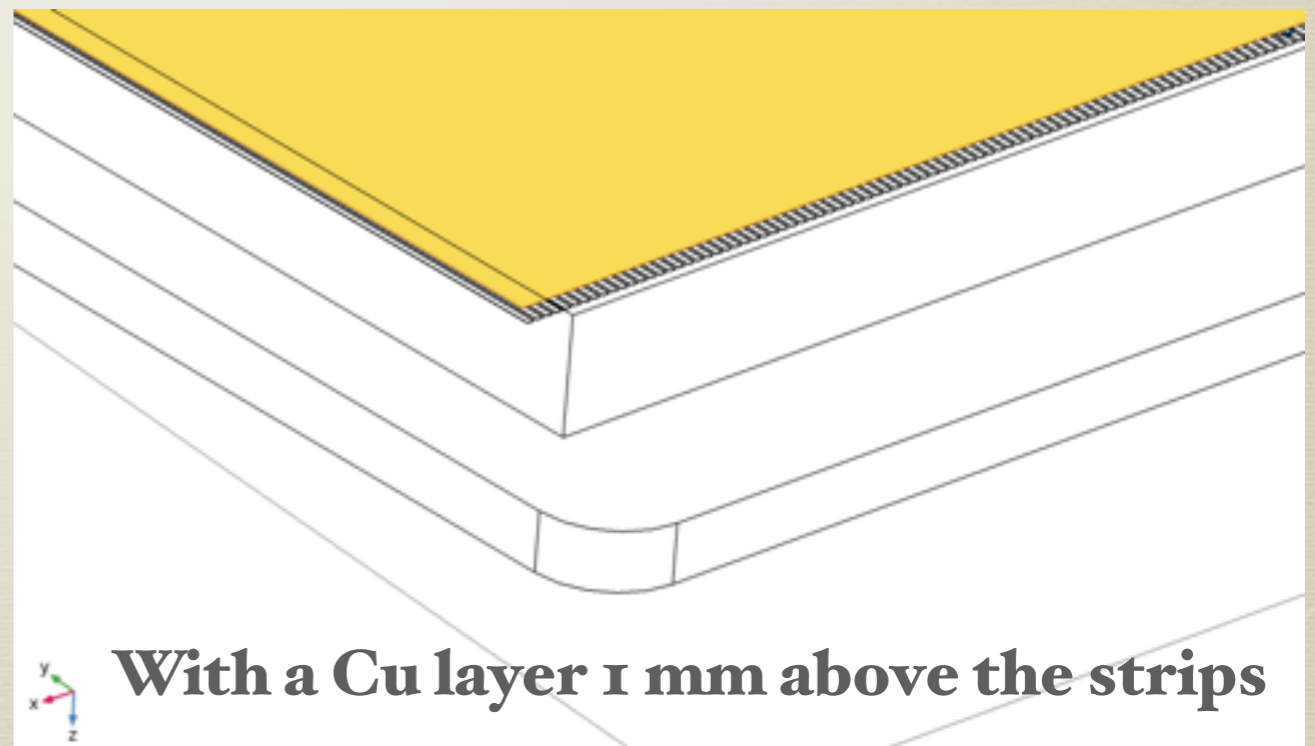
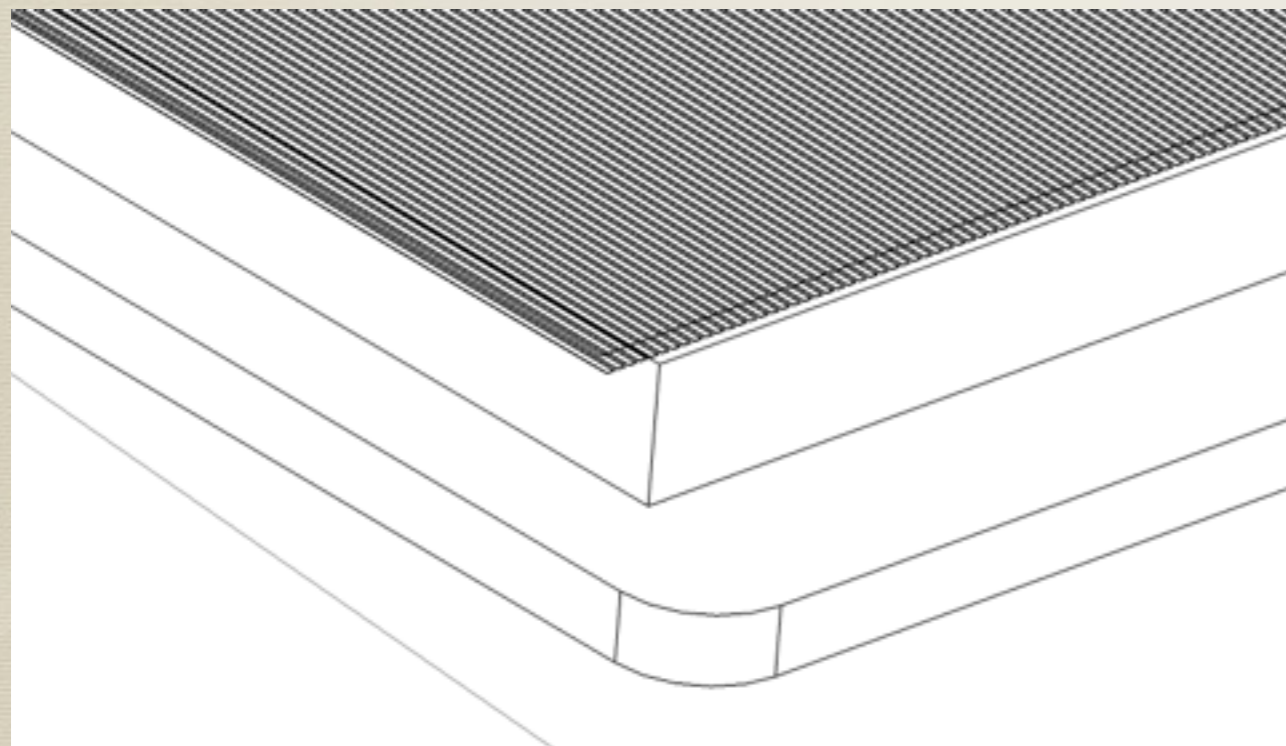
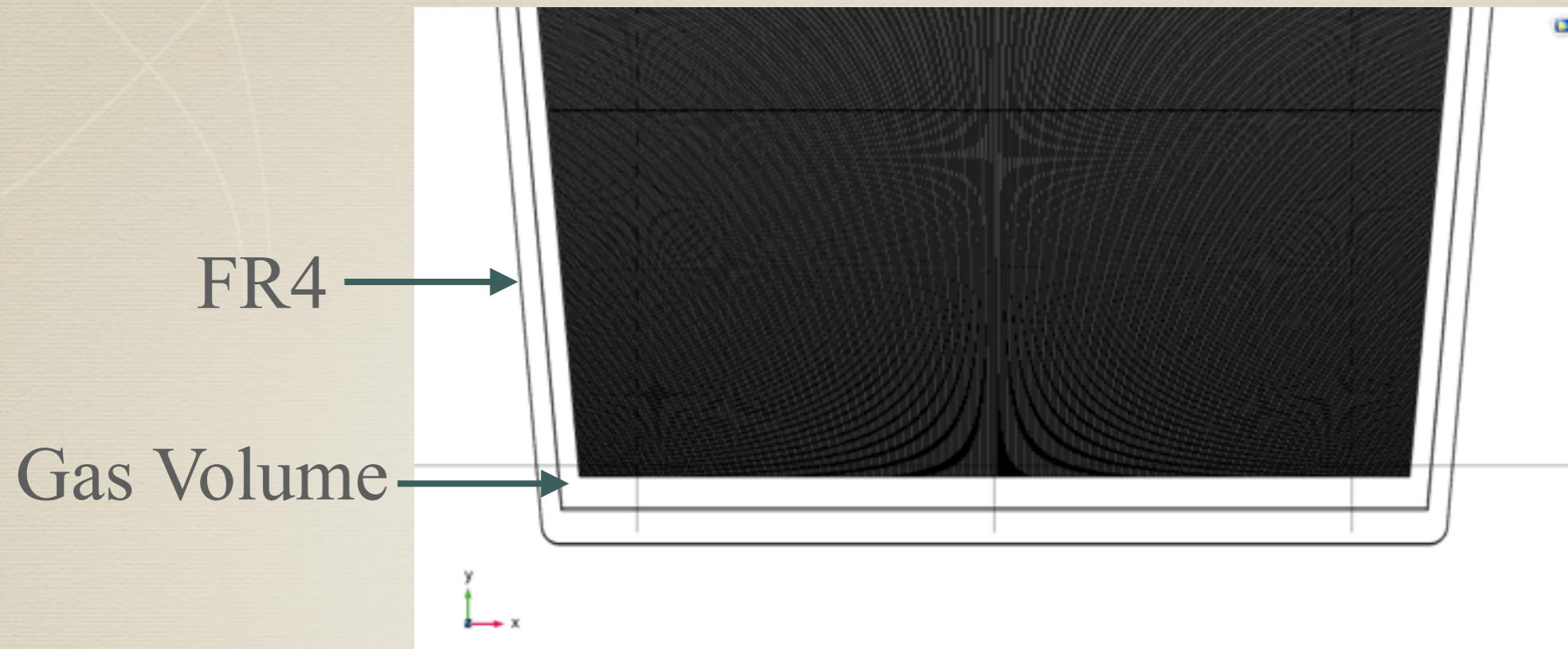
0.668

0.631



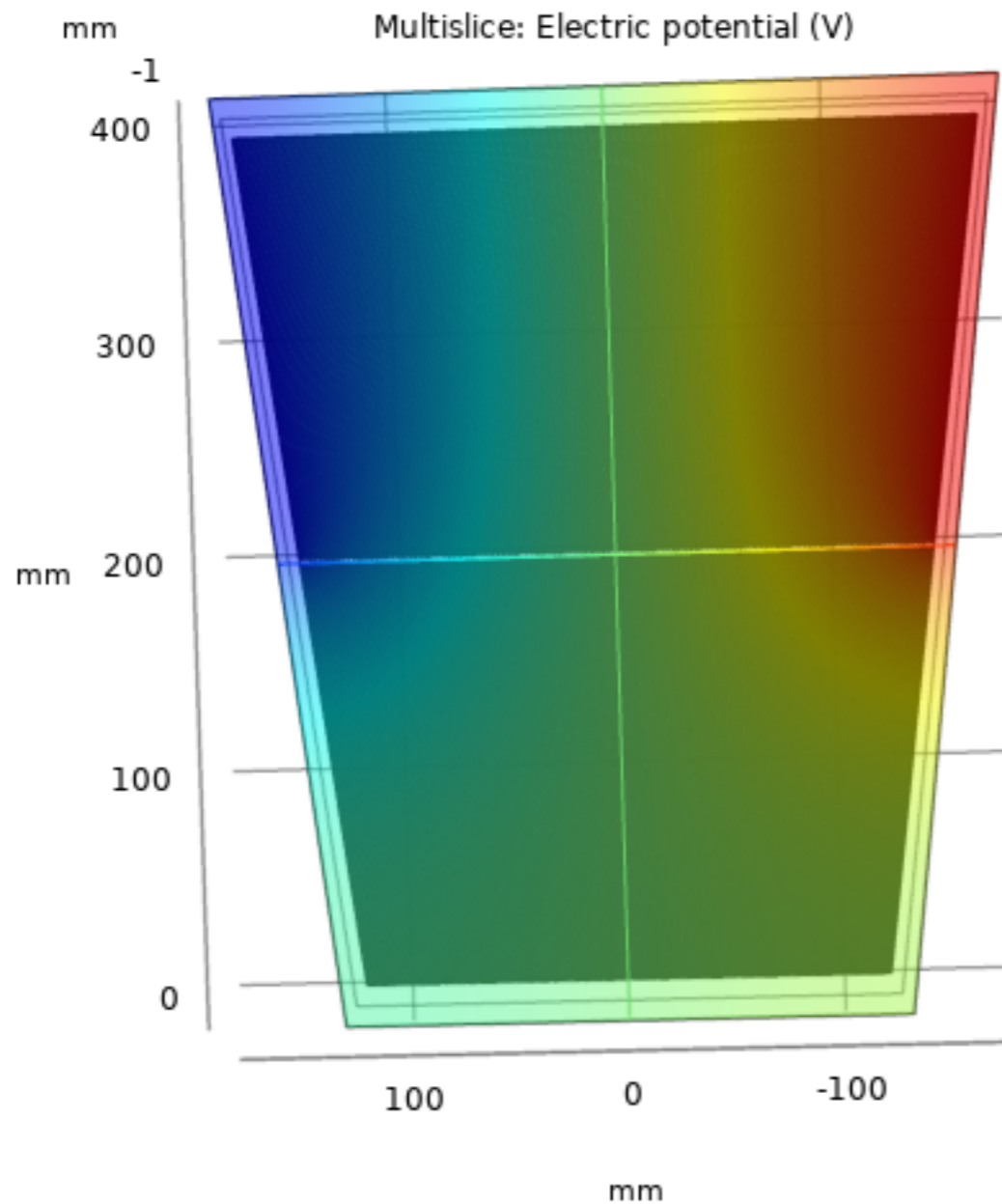


# Interstrip Capacitance (GE2/1)

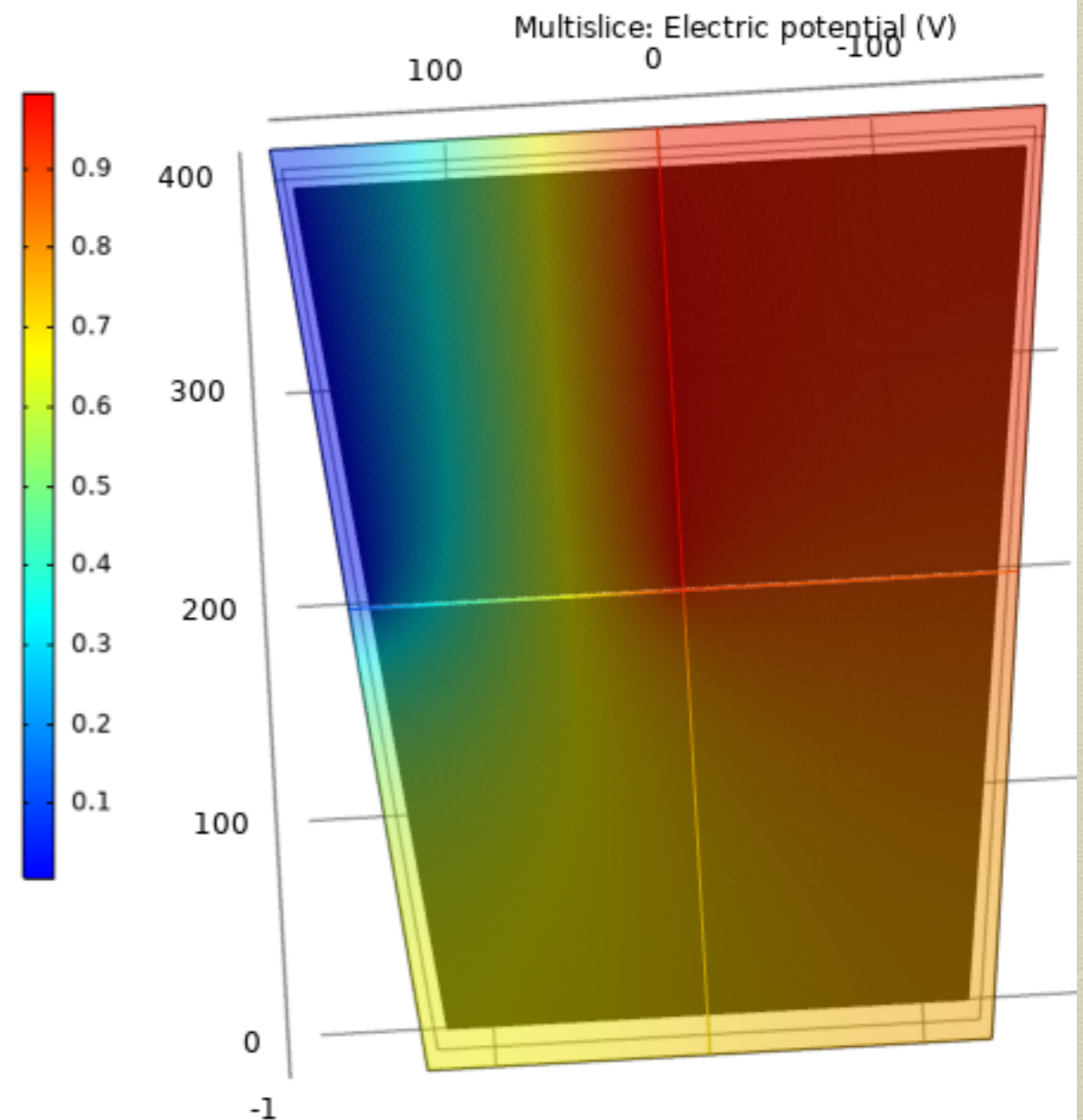


# Interstrip Capacitance (GE2/1)

MI module with a 5 $\mu$ m Cu layer 1 mm above the strips



Between strip 192 to 384  
0.0154 pF/cm



Between strip 1 to 384  
0.00838 pF/cm

# Interstrip Capacitance (GE2/1)

Table 4: GE2/1 ROB Interstrip Capacitance With and Without Grounding Plate

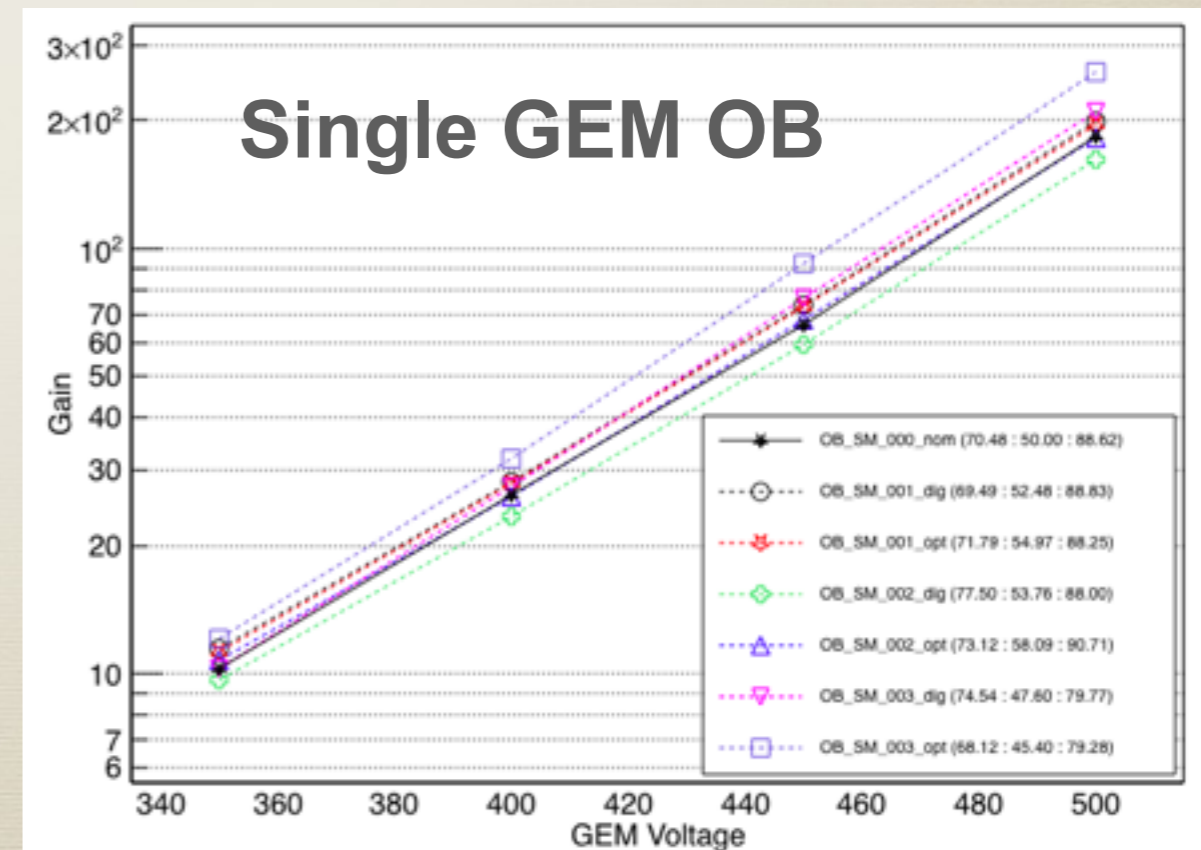
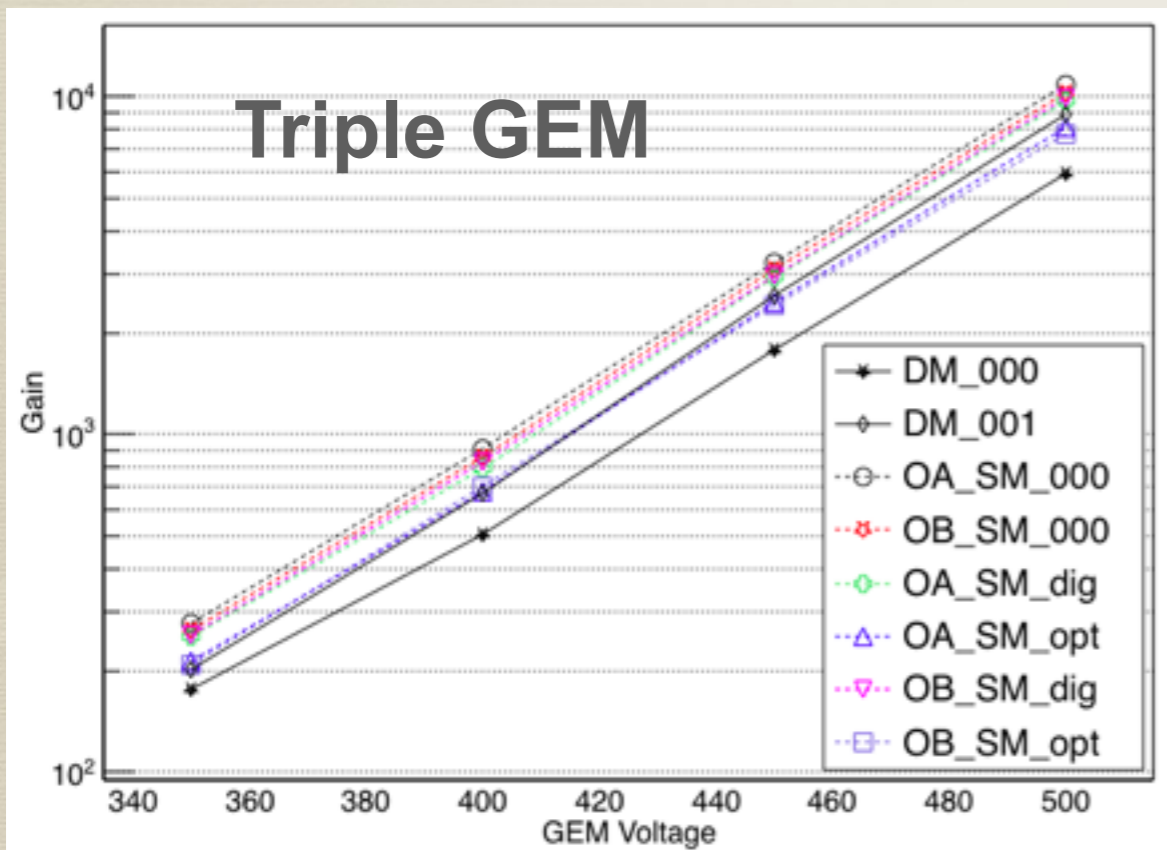
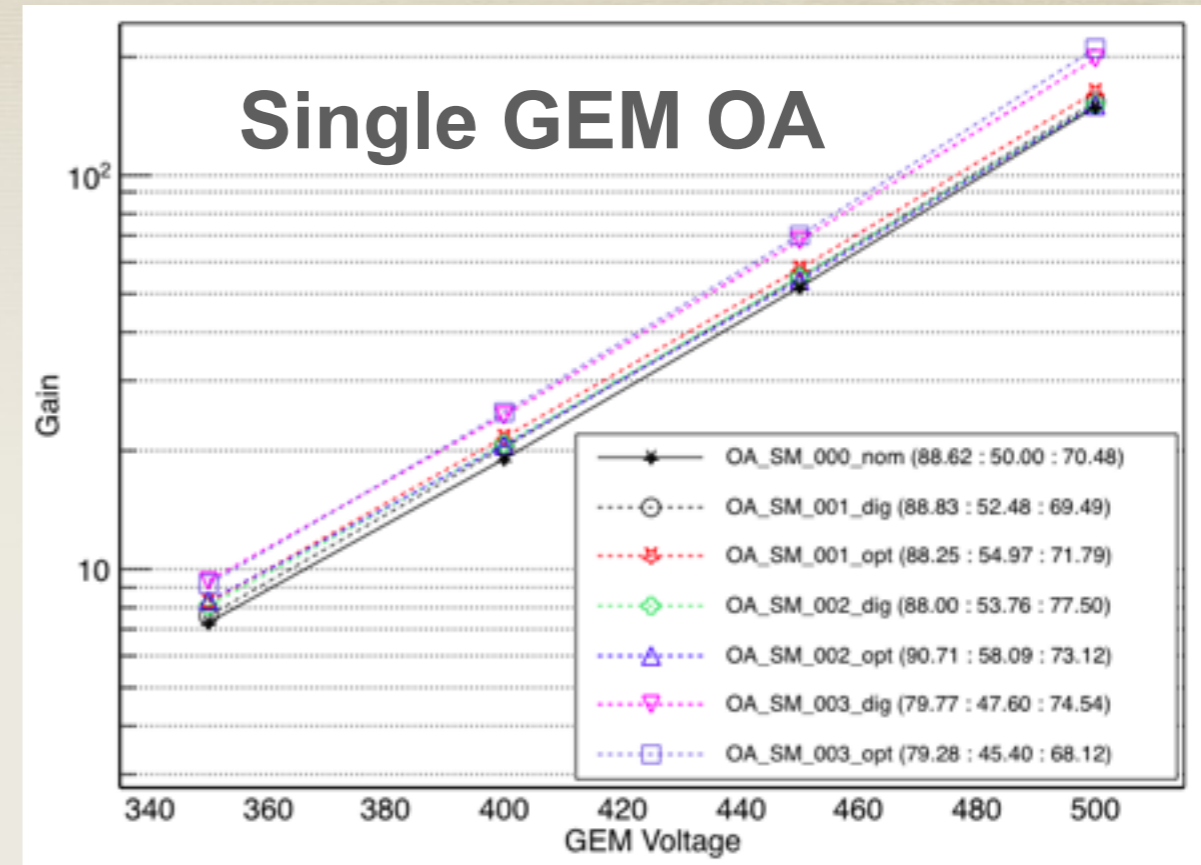
| Sector | Module | Parameters   | Avg. Meas. Cap.<br>w/o plate (pF) | Avg. Meas. Cap.<br>w/plate (pF) | $(C_w/C_{w/o})$ |
|--------|--------|--|-----------------------------------|---------------------------------|-----------------|
| 1      | M4     | Original TDR design (Strip Gap: 0.2 mm)                  | 21.69±0.05                        | 25.85±0.27                      | 1.192±0.013     |
| 2      | M4     | Gap: 0.3 mm  | 19.98±0.12                        | 20.98±0.03                      | 1.050±0.006     |
| 3      | M4     | 2×Width, 0.5×Length                                      | 15.33±0.03                        | 20.16±0.04                      | 1.315±0.004     |
| 4      | M4     | Long traces  | 27.87±0.06                        | 28.43±0.07                      | 1.020±0.003     |
| 5      | M1     | Original TDR design (Strip Gap: 0.2 mm)                  | 16.27±0.04                        | 19.04±0.21                      | 1.170±0.013     |
| 6      | M1     | Gap: 0.3 mm  | 14.65±0.07                        | 18.26±0.06                      | 1.246±0.007     |
| 7      | M1     | Gap: 0.4 mm  | 13.17±0.04                        | 14.85±0.08                      | 1.128±0.007     |
| 8      | M1     | 2×Width, 0.5×Length                                      | 11.82±0.06                        | 15.82±0.32                      | 1.338±0.028     |
| 9      | M1     | 0.5×Length   | 9.32±0.05                         | 9.17±0.10                       | 0.984±0.012     |
| 10     | M1     | Original TDR Design, Long traces                         | 20.58±0.06                        | 26.80±0.14                      | 1.302±0.008     |
| 11     | M1     | Original TDR Design, Minimal traces                      | 14.02±0.02                        | 14.82±0.03                      | 1.057±0.003     |
| 12     | M1     | Original TDR Design, Minimal traces, 0.5×Length, 2×Width | 10.39±0.07                        | 10.33±0.11                      | 0.994±0.013     |

| Module | Parameters              | Cap. w/o plate<br>(pF) | Cap. with plate<br>(pF) | C     |
|--------|-------------------------|------------------------|-------------------------|-------|
| M4     | Strip Gap: 0.2mm        | 16.119                 | 16.252                  | 1.008 |
| M4     | 2 x Width, 0.5 x Length | 12.635                 | 12.691                  | 1.004 |
| M1     | Strip Gap: 0.2mm        | 13.159                 | 13.607                  | 1.034 |
| M1     | 0.5 x Length            | 7.0076                 | 7.1788                  | 1.024 |

Working with other parameters

# Hole size Variation

- Single and triple GEM with both single mask & double mask configuration
- Simulate & estimate the variation in gain due to different hole size
- Obtained different hole geometry from digital and optical microscopy from Jeremie



# Hole size Variation

## CMS Internal Note

The content of this note is intended for CMS internal use and distribution only

01 October 2019

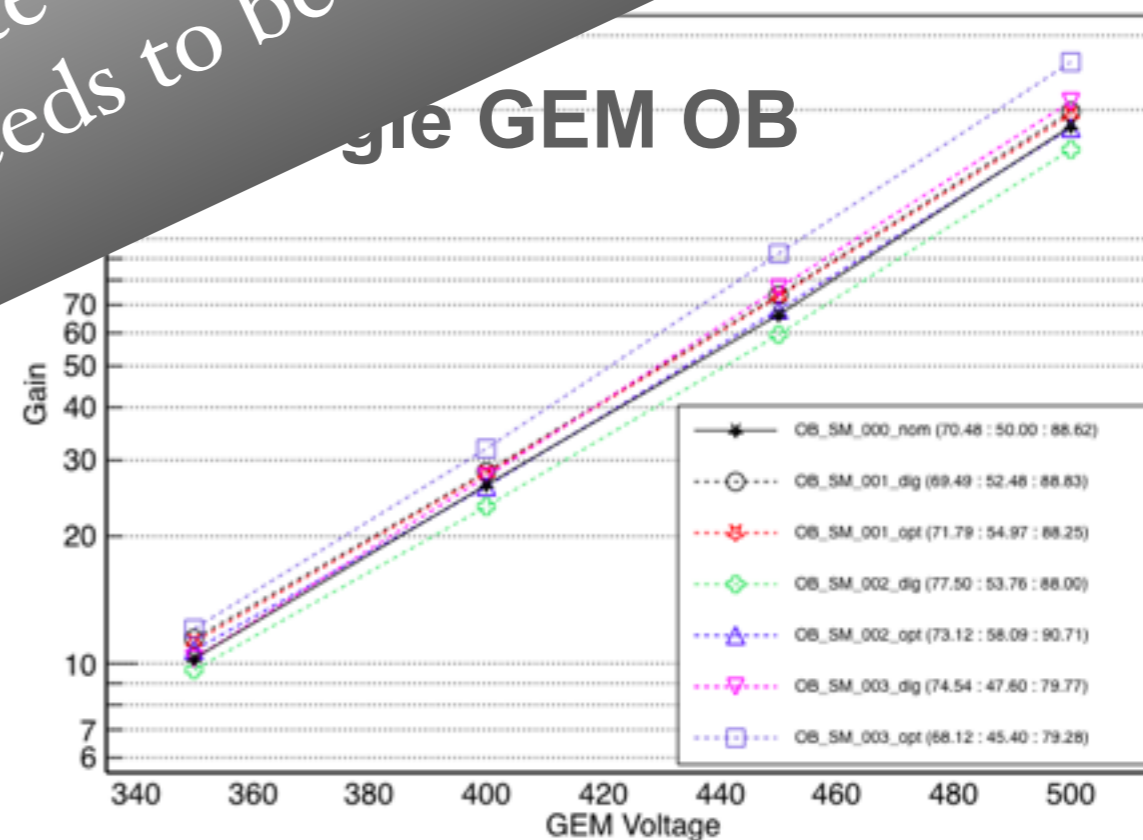
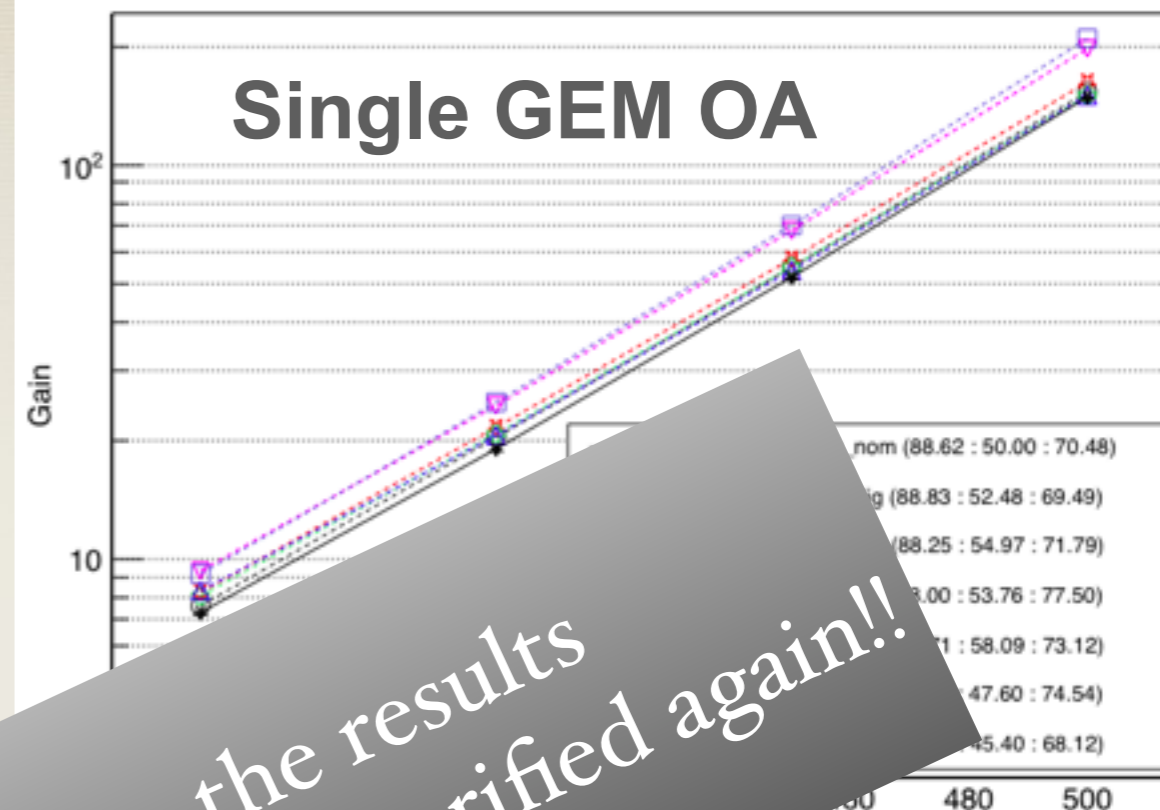
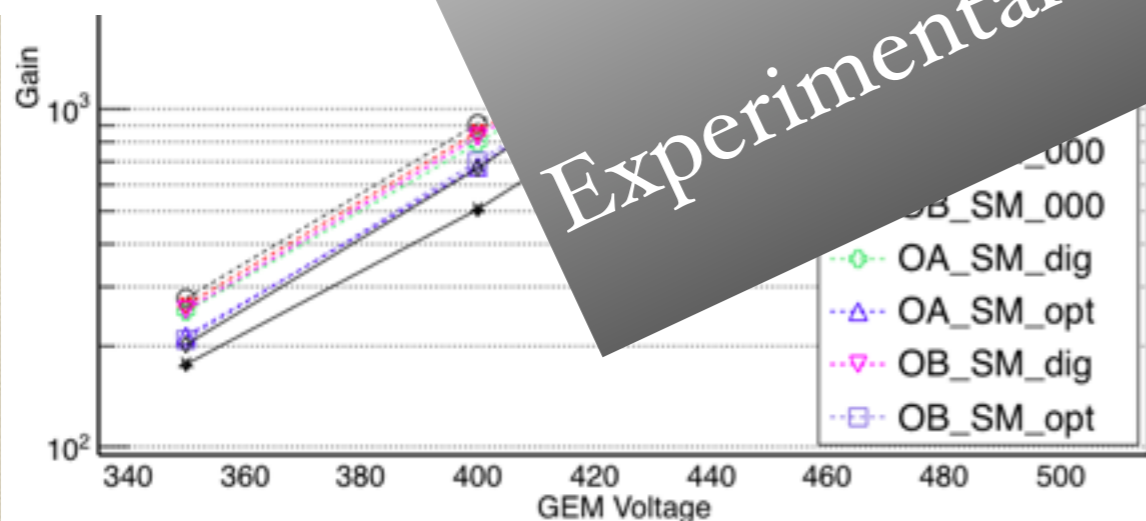
### Simulation study of triple GEM detectors due to hole asymmetry on foils

Othmane Bouhali, Shivali Malhotra

**Final list of authors will be fixed later**

#### Abstract

The Gas Electron Multiplier (GEM) is an amplification stage that has been introduced to solve the problem of discharges observed in gaseous detectors. There are two major configurations for the GEM foils: double mask and single mask. Despite being an effective solution, a hole size variation is observed between the top and bottom diameters of GEM holes in the double mask configuration. In this paper we conduct an extensive simulation study on double mask based detectors. To characterize the properties of the detectors, simulations are performed with Garfield++ simulation package. The effect of hole size variation on the gain and the meshing needed for the field simulation are also compared with an experimental result.

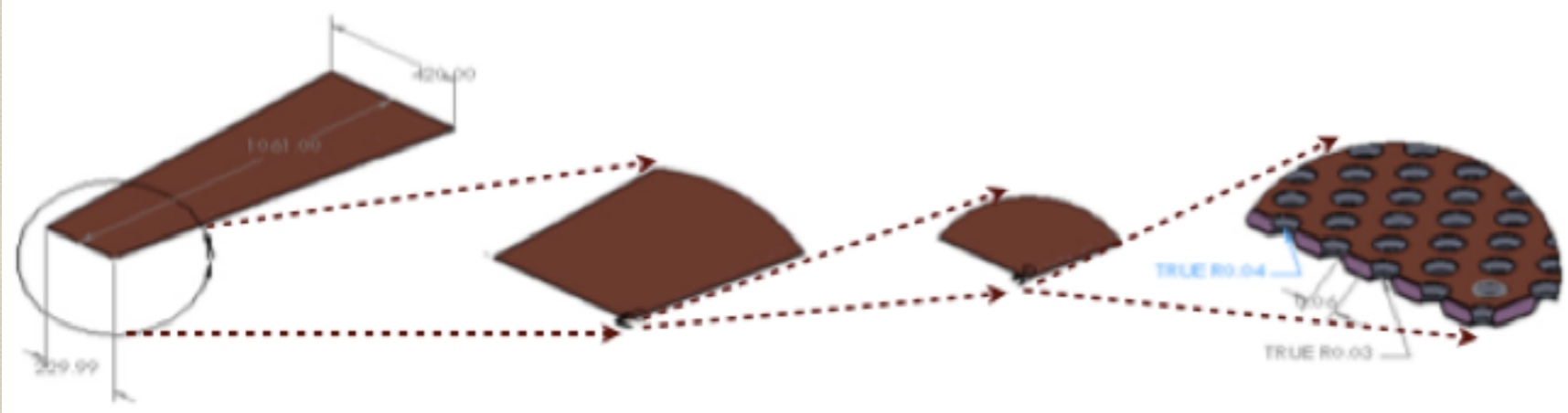
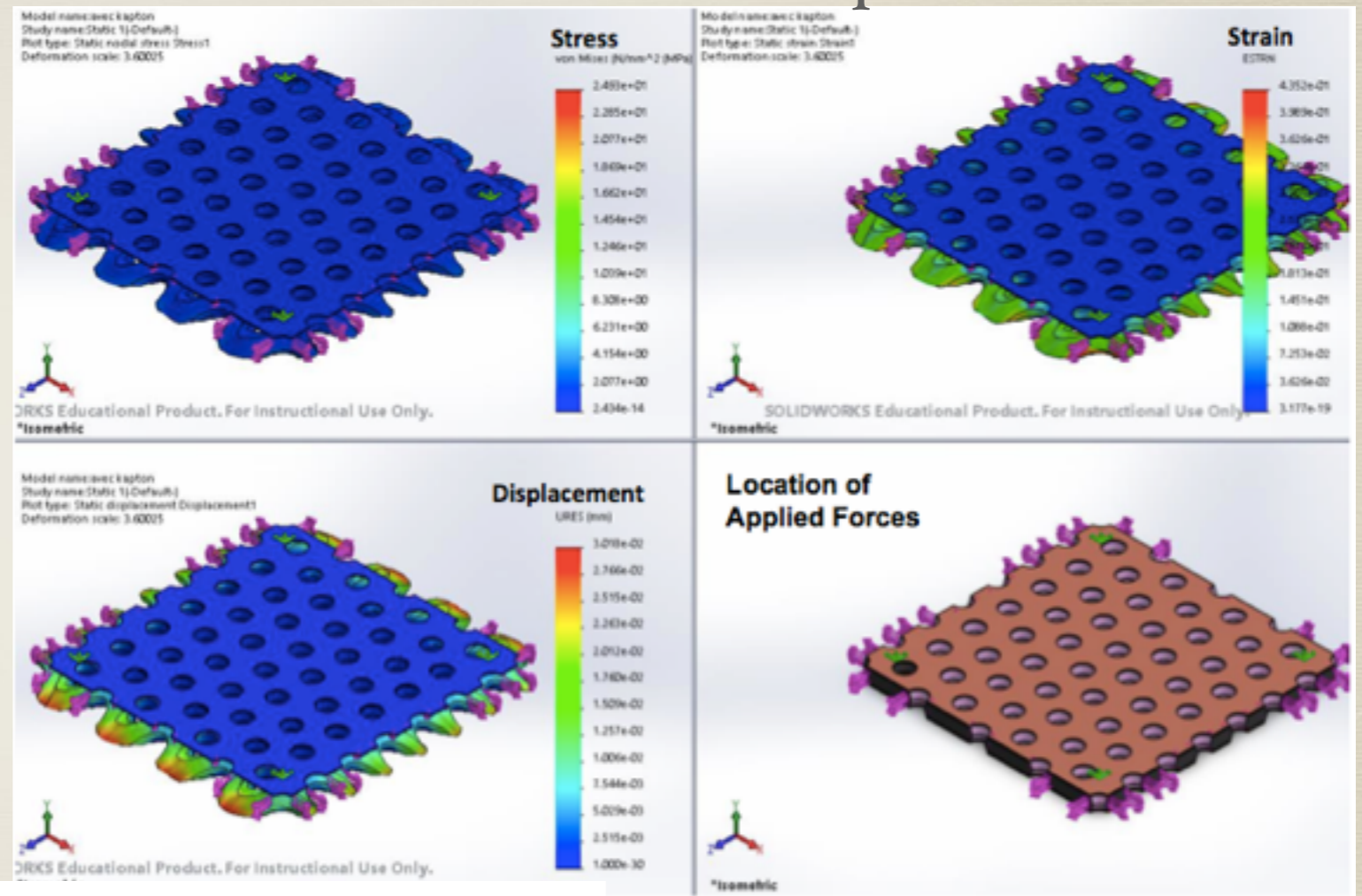


Submitted a Note on the results  
Experimental result needs to be verified again!!

# Deformation of Foil due to Stretching

Stretching force applied on 1mm x 1mm GEM foil sample

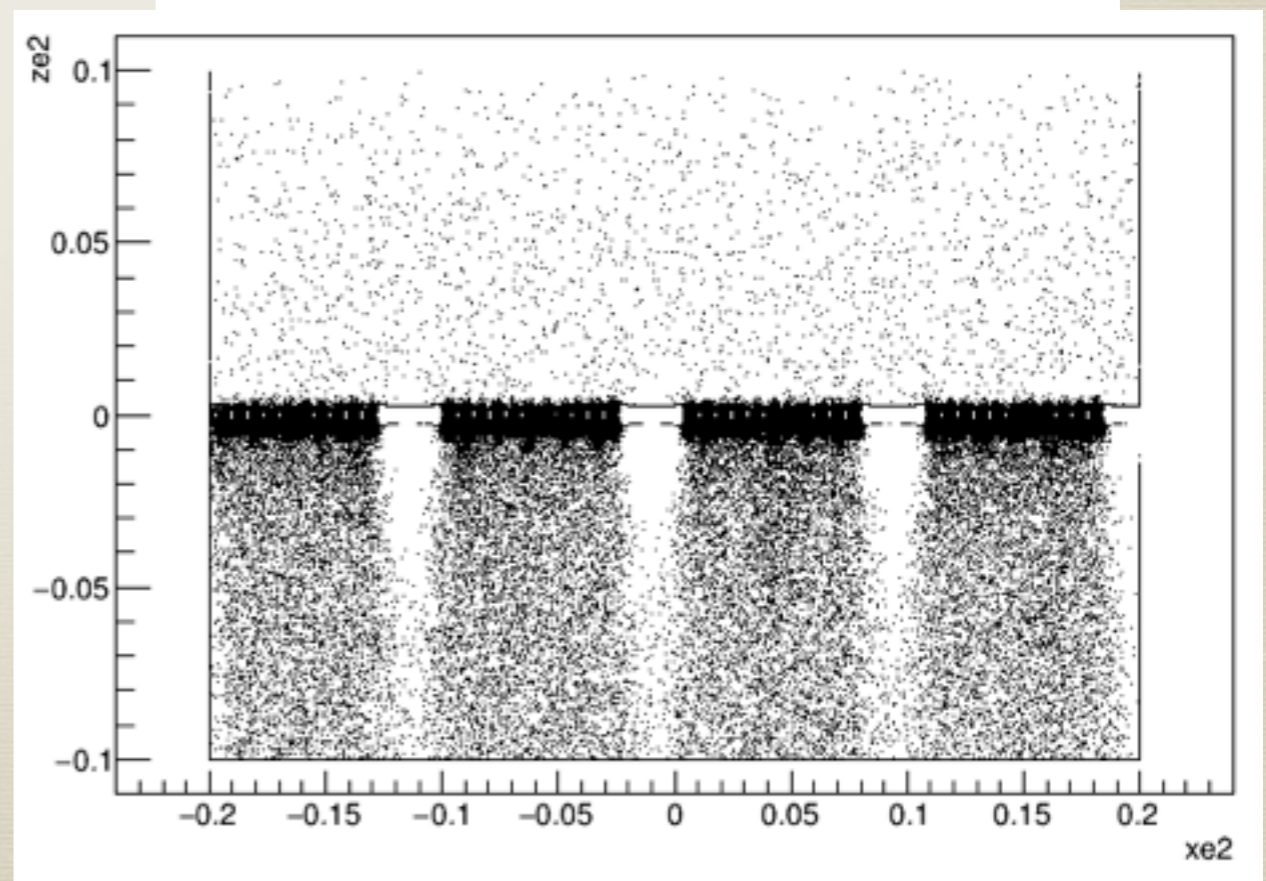
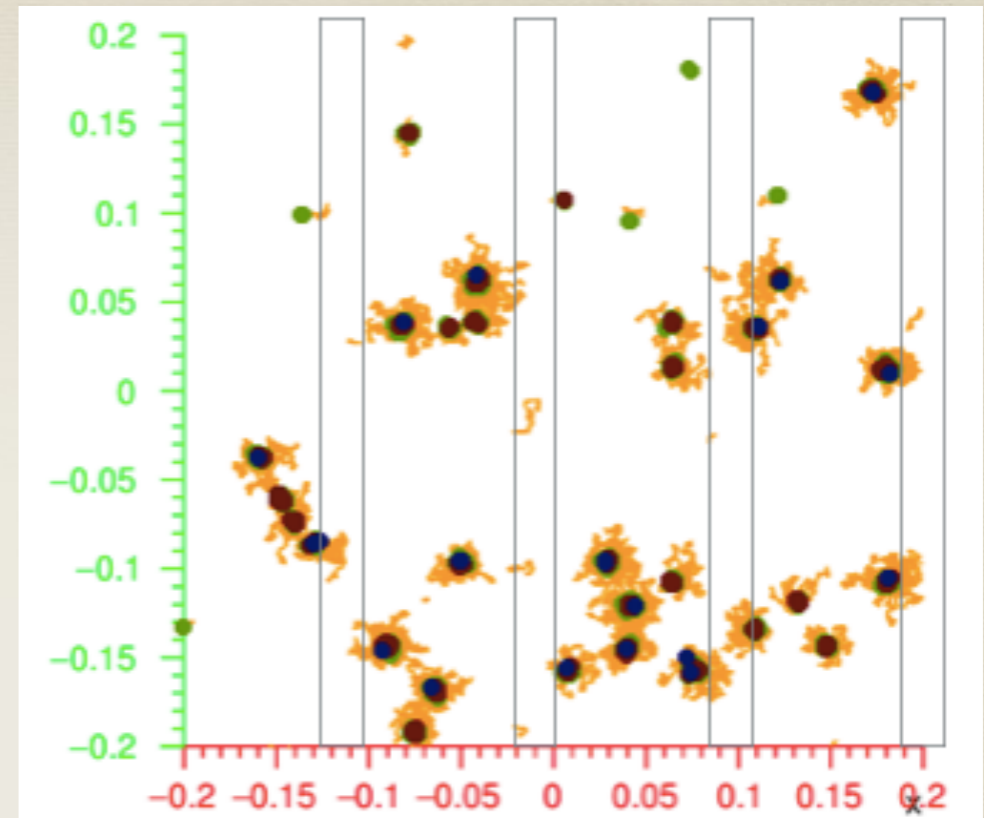
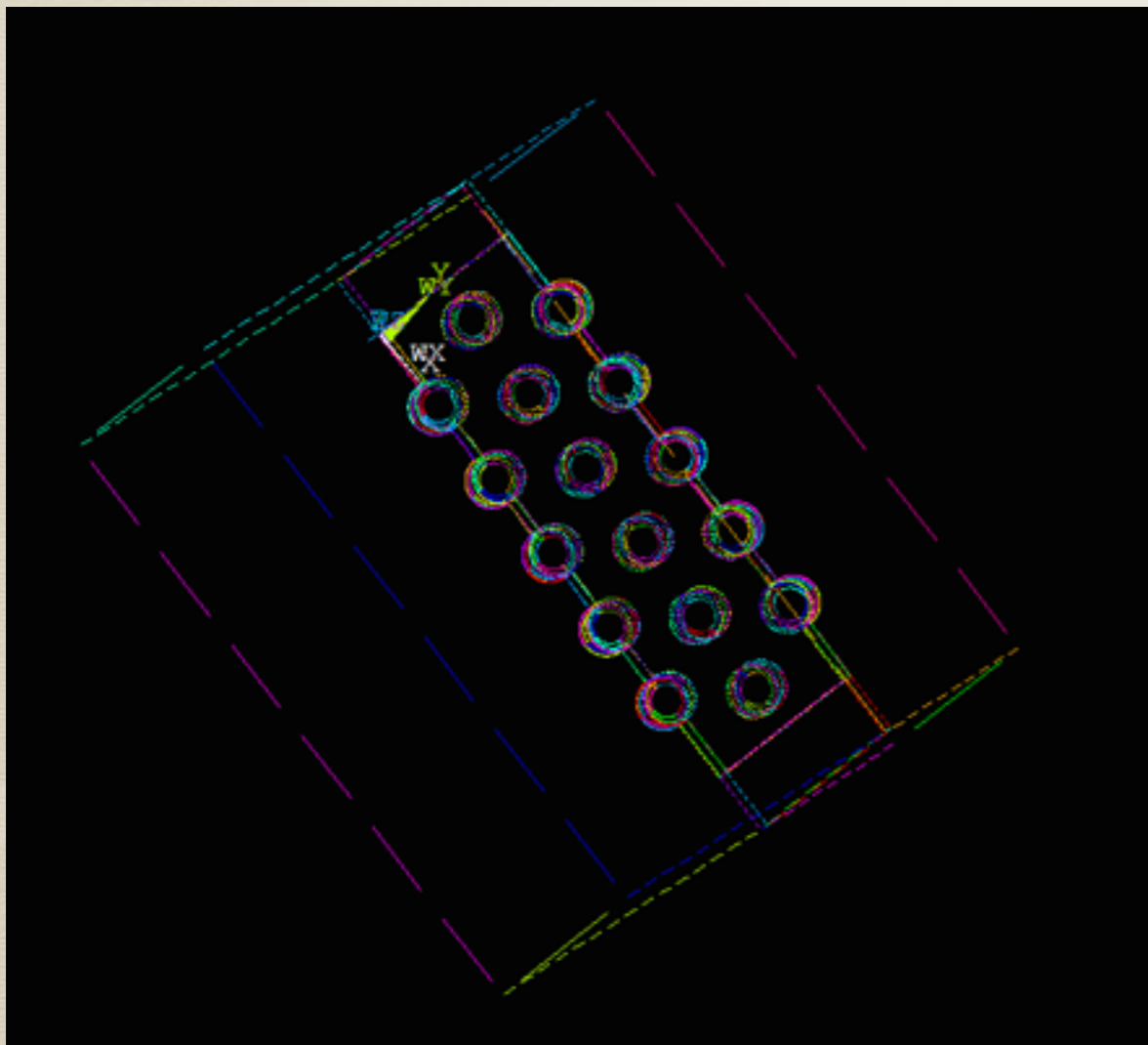
- Build a Finite Element Model (FEM) for a small area GEM foil (done in SolidWorks)
- Estimate the deformation on the holes due to force applied in x & y directions
- Extrapolate the results to large area GEM foil



FEM was built for GE1/I chambers

# Dead Area Simulation

- Base element created in ANSYS
- Extended simulation area to 4mm x 4mm
- Dead Area:  $-0.124$  to  $-0.104$ ;  $-0.02$  to  $0$  ;  $0.084$  to  $0.104$  and  $0.188$  to  $0.2$



# Summary

- For GE1/1 Operation we are performing the simulation to understand the dissipation of heat from a discharge.
- Trying to debug the issue generated with a point source.
- Simulated values of Interstrip Capacitance are in good agreement with the measured values for both GE1/1 & GE2/1.
- Note has been submitted related to the study of gain variation due to asymmetry in hole size.
- Other ongoing simulation studies have been reported

**READY TO BE  
REVIEWED!!**